## 2SA2028

## Silicon PNP epitaxial planar type

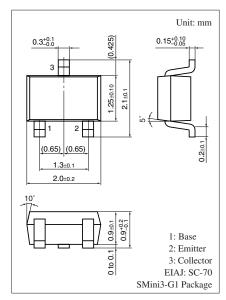
#### For DC-DC converter

#### ■ Features

- Low collector-emitter saturation voltage V<sub>CE(sat)</sub>
- High-speed switching
- S-Mini type package, allowing downsizing and thinning of the equipment and automatic insertion through the tape packing

### $\blacksquare$ Absolute Maximum Ratings $T_a = 25 ^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-20	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-20	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V	
Collector current	$I_C$	-1	A	
Peak collector current	$I_{CP}$	-3	A	
Collector power dissipation	P <sub>C</sub>	150	mW	
Junction temperature	$T_j$	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +125	°C	



Marking Symbol: AT

### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_C = -10 \ \mu A, \ I_E = 0$	-20			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -1 \text{ mA}, I_{\rm B} = 0$	-20			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -10 \ \mu A, I_C = 0$	-5			V
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = -2 \text{ V}, I_{C} = -100 \text{ mA}$	160		560	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -200 \text{ mA}, I_B = -10 \text{ mA}$		-40	-100	mV
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$		170		MHz
Collector output capacitance	Cob	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		20	30	pF
(Common base, input open circuited)						

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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